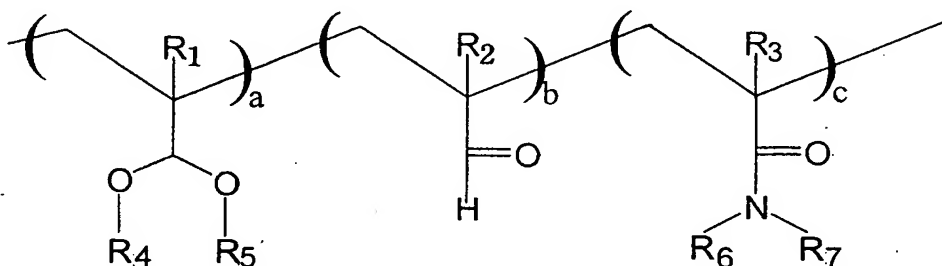


ABSTRACT OF THE DISCLOSURE

Photoresist polymers and photoresist compositions containing the same are disclosed. A negative photoresist composition containing a photoresist polymer comprising a repeating unit represented by Formula 4 prevents collapse of patterns when photoresist patterns of less than 50nm are formed. Accordingly, the disclosed negative photoresist composition is very effective for a photolithography process using EUV (Extreme Ultraviolet, 13nm) light source.

Formula 4



wherein R₁, R₂, R₃, R₄, R₅, R₆, R₇, a, b and c are as defined in the description.